

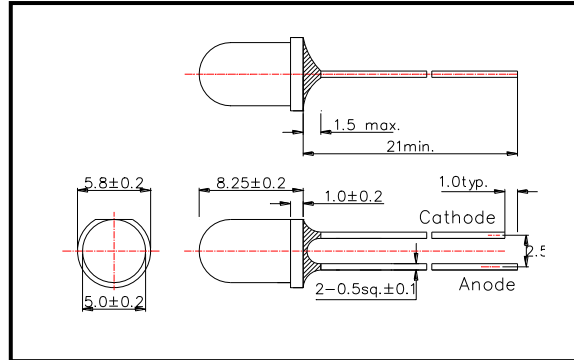
L1070-03 Infrared LED Lamp

L1070-03 is an InGaAsP LED mounted on a lead frame with a clear epoxy lens. On forward bias, it emits a spectral band of radiation, which peaks at 1070nm.

◆ Specifications

- 1) Product Name Infrared LED Lamp
- 2) Type No. L1070-03
- 3) Chip
- (1) Chip Material InGaAsP
- (2) Peak Wavelength 1070nm typ.
- 4) Package
- (1) Type Φ5mm epoxy molding
- (2) Resin Color Clear color
- (3) Lead Frame Soldered (Lead Free)

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	140	mW	T _a =25°C
Forward Current	I _F	100	mA	T _a =25°C
Pulse Forward Current	I _{FP}	1000	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Junction Temperature	T _J	100	°C	
Thermal Resistance	R _{thjp}	340	K/W	
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

‡Thermal resistance: junction – ambient, leads 7mm, soldered on PCB.

◆ Electro-Optical Characteristics [T_a=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =20mA		1.05	1.25	V
		I _F =50mA		1.15	1.35	
Radiated Power	P _O	I _F =20mA	1.7	3.2		mW
		I _F =50mA	4.0	7.5		
Radiant Intensity	I _E	I _F =20mA		1.5		mW/sr
		I _F =50mA		3.5		
Peak Wavelength	λ _P	I _F =50mA	(1050)	1070	(1090)	nm
Half Width	Δλ	I _F =50mA		50		nm
Centroid Wavelength	λ _C	I _F =50mA		1060		
Viewing Half Angle	θ _{1/2}	I _F =50mA		±15		deg.
Rise Time	t _r	I _F =50mA		10		ns
Fall Time	t _f	I _F =50mA		10		ns

‡Total Radiated Power is measured by G8370-85

‡Radiated Power is measured by Ando Optical Multi Meter AQ2140 & AQ2743

‡ () means target spec on QC wavelength

